



#### **40V P-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-40V	80mΩ @ V <sub>GS</sub> = -10V	-3.7 A
-40 V	150mΩ @ V <sub>GS</sub> = -4.5V	-2.8 A

#### Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

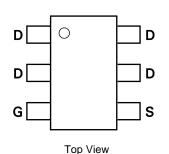
### **Features and Benefits**

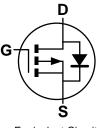
- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.018 grams (Approximate)







Equivalent Circuit

#### Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Quantity per reel
ZXMP4A57E6TA	Standard	SOT26	3,000
ZXMP4A57E6QTA	Automotive	SOT26	3,000

Pin-Out

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

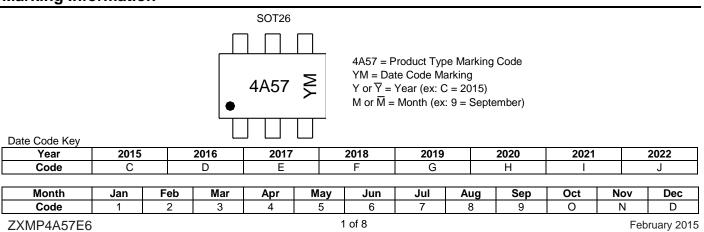
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

Notes:



Document Number DS35238 Rev. 3 - 2



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	-40	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	V	
		(Note 7)		-3.7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C$ (Note 7)	ID	-2.9	А
		(Note 6)		-2.9	
Pulsed Drain Current	$V_{GS} = 10V$	(Note 8)	IDM	-18	А
Continuous Source Current	(Body Diode)	(Note 7)	Is	-2.6	А
Pulsed Source Current (Bod	y Diode)	(Note 8)	I <sub>SM</sub>	-18	А

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)		1.1 8.8	W mW/°C	
Linear Derating Factor	(Note 7)	– P <sub>D</sub>	1.7 13.7		
Thermal Desistance, Junction to Ambient	(Note 6)	D	113	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>θJA</sub>	73	C/W	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

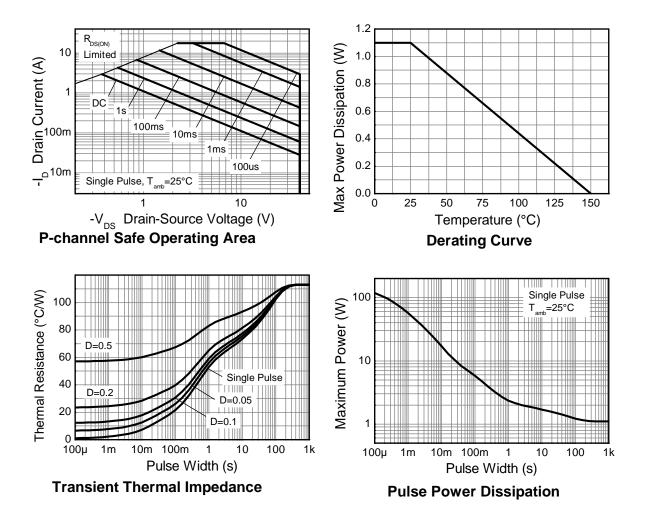
Notes: 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

7. Same as Note 4, except the device is measured at t  $\leq$  5 seconds.

8. Same as Note 4, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.



## **Thermal Characteristics**





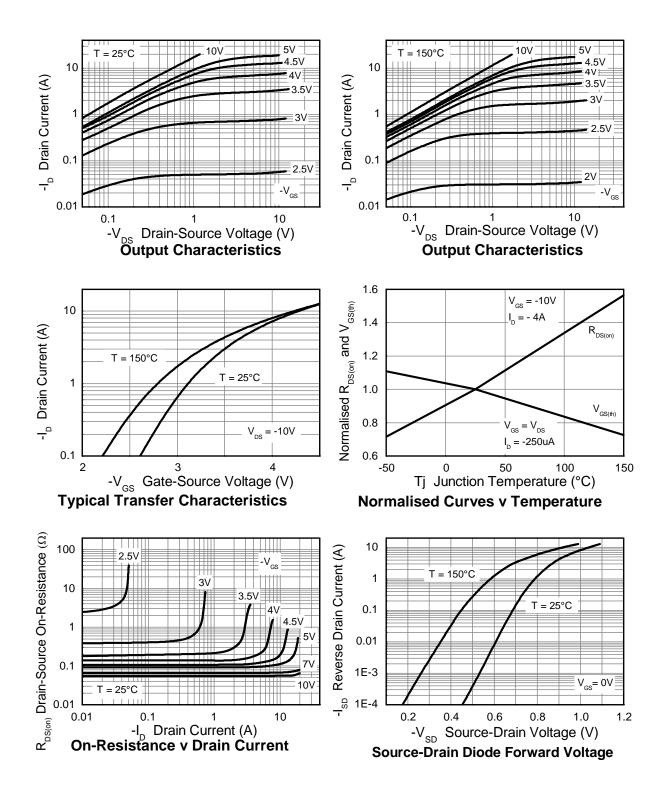
#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition
OFF CHARACTERISTICS				•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40		—	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		-0.5	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—	-3.0	V	$I_D = -250 \mu A, V_I$	os = V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 9)	Р	_		0.080	Ω	$V_{GS} = -10V, I_D = -4A$	
Static Drain-Source On-Resistance (Note 9)	R <sub>DS(ON)</sub>	_		0.150	12	$V_{GS}$ = -4.5V, $I_D$	= -2A
Forward Transconductance (Notes 9 & 10)	<b>g</b> fs	—	7.6		S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -4A	
Diode Forward Voltage (Note 9)	V <sub>SD</sub>	_	-0.86	-0.95	V	$I_{\rm S} = -4$ A, $V_{\rm GS} = 0$ V	
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	_	17.4	_	ns	I <sub>S</sub> = -1.8A, di/dt = 100A/µs	
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	_	11.1	_	nC		
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	833	_		$pF \qquad \begin{cases} V_{DS} = -20V, V_{GS} = 0V \\ f = 1MHz \end{cases}$	
Output Capacitance	C <sub>oss</sub>	_	122	_	pF		
Reverse Transfer Capacitance	Crss	_	78	_			
Total Gate Charge (Note 11)	Qg	_	7	_		V <sub>GS</sub> = -4.5V	
Total Gate Charge (Note 11)	Qg	_	15.8	_	nC		V <sub>DS</sub> = -20V
Gate-Source Charge (Note 11)	Q <sub>gs</sub>	_	3.6	_	nc	$V_{GS} = -10V$ $I_D = -4A$	$I_D = -4A$
Gate-Drain Charge (Note 11)	Q <sub>gd</sub>	_	2.7	—			
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>	_	2.5	_		ns $V_{DD} = -20V, V_{GS} = -10V$ $I_D = -1A, R_G \cong 6.0\Omega$	
Turn-On Rise Time (Note 11)	tr		3.3	_			
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>	_	47		115		
Turn-Off Fall Time (Note 11)	t <sub>f</sub>	_	21	_			

9. Measured under pulsed conditions. Pulse width  $\leq$  300µs; duty cycle  $\leq$  2%. 10. For design aid only, not subject to production testing. 11. Switching characteristics are independent of operating junction temperatures. Notes:

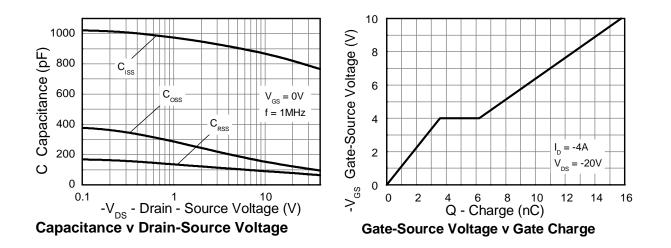


# **Typical Characteristics**

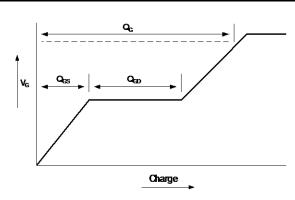




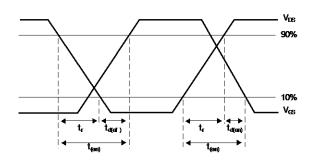
## Typical Characteristics (cont.)



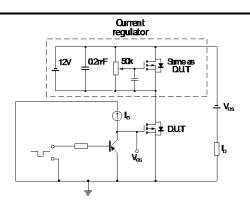
**Test Circuits** 



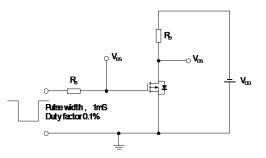
Basic gate charge waveform



Switching time waveforms



Gate charge test circuit

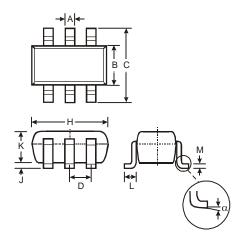


Switching time test circuit



### **Package Outline Dimensions**

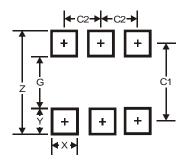
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D	_		0.95		
н	2.90	3.10	3.00		
J	0.013 0.10		0.05		
κ	1.00 1.30 1.1		1.10		
L	0.35 0.55 0.4		0.40		
М	0.10 0.20		0.15		
α	α 0° 8° —				
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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